

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
Channel-1	30	0.0160 at V _{GS} = 10 V	8.0 ^e	19
		0.0186 at V _{GS} = 4.5 V	8.0 ^e	
Channel-2	30	0.0264 at V _{GS} = 10 V	8.0 ^e	6
		0.0290 at V _{GS} = 4.5 V	8.0 ^e	

FEATURES

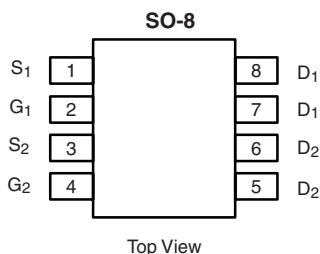
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET® Monolithic TrenchFET® Power MOSFET and Schottky Diode
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



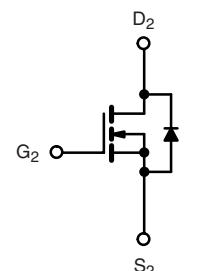
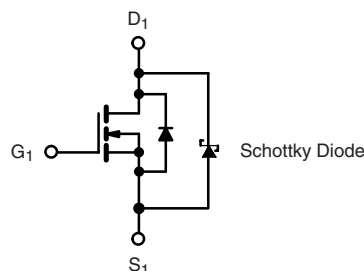
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Notebook Logic DC-DC
- Low Current DC-DC



Ordering Information: Si4622DY-T1-E3 (Lead (Pb)-free)
Si4622DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage		V _{DS}	30	30	V
Gate-Source Voltage		V _{GS}	± 20	± 16	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	8 ^e	8 ^e	A
	T _C = 70 °C		8 ^e	6.7	
	T _A = 25 °C		8 ^{b, c, e}	6.7 ^{b, c}	
	T _A = 70 °C		7.2 ^{b, c}	5.3 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	60	30	
Source-Drain Current Diode Current	T _C = 25 °C	I _S	2.8	2.6	
	T _A = 25 °C		1.8 ^{b, c}	1.7 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	25	15	mJ
Single Pulse Avalanche Energy		E _{AS}	31.2	11.2	
Maximum Power Dissipation	T _C = 25 °C	P _D	3.3	3.1	W
	T _C = 70 °C		2.1	2.0	
	T _A = 25 °C		2.2 ^{b, c}	2.0 ^{b, c}	
	T _A = 70 °C		1.4 ^{b, c}	1.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	45	56	55	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	29	38	33	40	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 110 °C/W (Channel-1) and 110 °C/W (Channel-2).

e. Package limited.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30			V	
		V _{GS} = 0 V, I _D = 250 μA	Ch-2	30				
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	Ch-2		33		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	Ch-2		- 4.7			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 mA	Ch-1	1.5		2.5	V	
		V _{DS} = V _{GS} , I _D = 1 mA	Ch-2	1		2.2		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	Ch-1			100	nA	
		V _{DS} = 0 V, V _{GS} = ± 16 V	Ch-2			100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1		0.04	0.2	mA	
		V _{DS} = 30 V, V _{GS} = 0 V	Ch-2			1		μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C	Ch-1		4.4	44	mA	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C	Ch-2			5		μA
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-1	25			A	
		V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-2	20				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 9.6 A	Ch-1		0.0132	0.0160	Ω	
		V _{GS} = 10 V, I _D = 6.7 A	Ch-2		0.022	0.0264		
		V _{GS} = 4.5 V, I _D = 8.9 A	Ch-1		0.0155	0.0186		
		V _{GS} = 4.5 V, I _D = 6.4 A	Ch-2		0.0240	0.0290		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 9.6 A	Ch-1		94		S	
		V _{DS} = 15 V, I _D = 6.7 A	Ch-2		10			
Dynamic ^a								
Input Capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		2458		pF	
			Ch-2		760			
Output Capacitance	C _{oss}	Channel-2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		385			
			Ch-2		110			
Reverse Transfer Capacitance	C _{rss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		150		nC	
			Ch-2		50			
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 9.6 A	Ch-1		40	60	nC	
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 6.7 A	Ch-2		13.2	20		
Gate-Source Charge	Q _{gs}	Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 9.6 A	Ch-1		19	29		
			Ch-2		6	12		
Gate-Drain Charge	Q _{gd}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 6.7 A	Ch-1		8			
			Ch-2		2.1			
Gate Resistance	R _g	f = 1 MHz	Ch-1	0.26	1.3	2.6		Ω
			Ch-2	0.62	3.1	6.2		



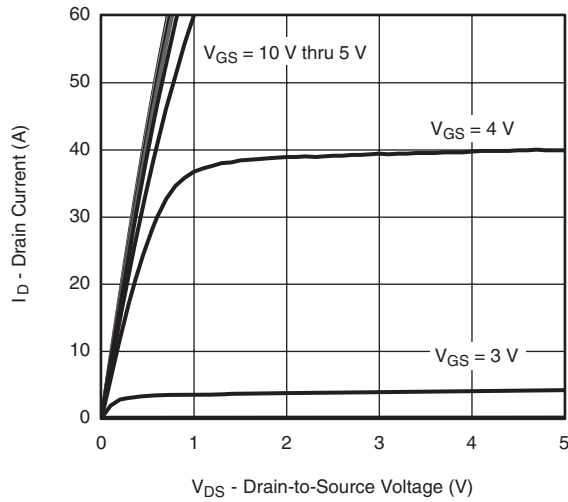
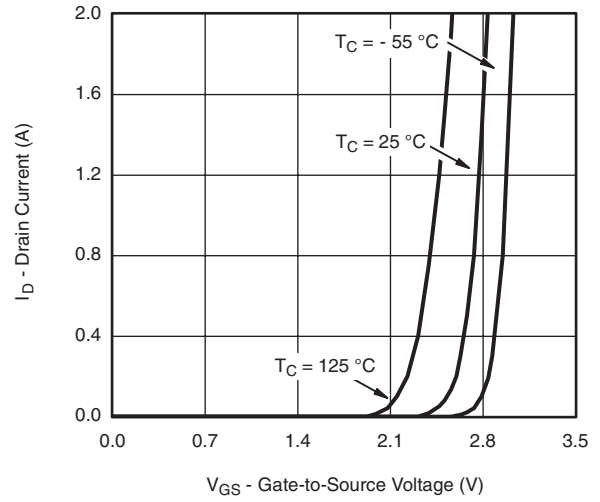
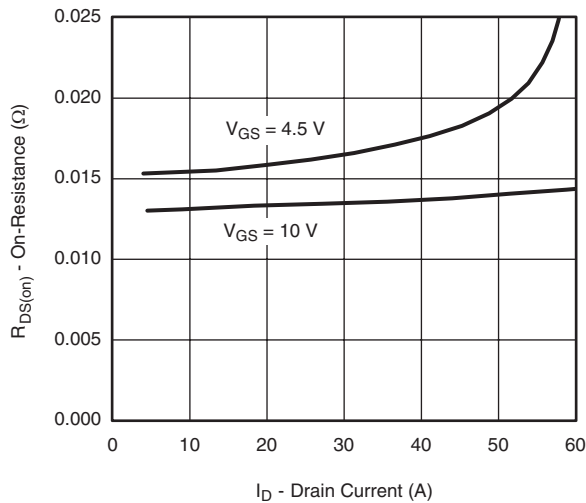
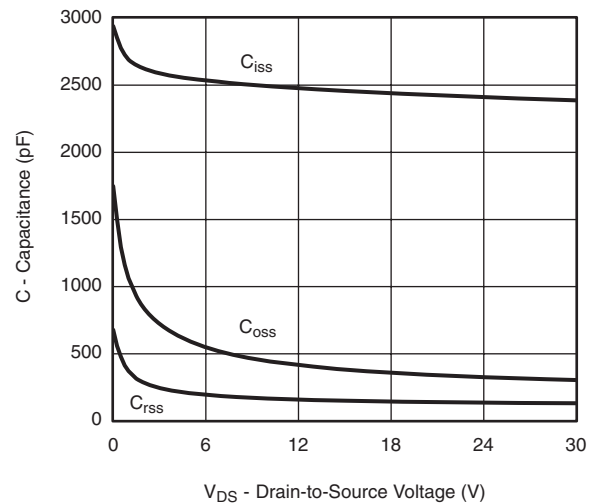
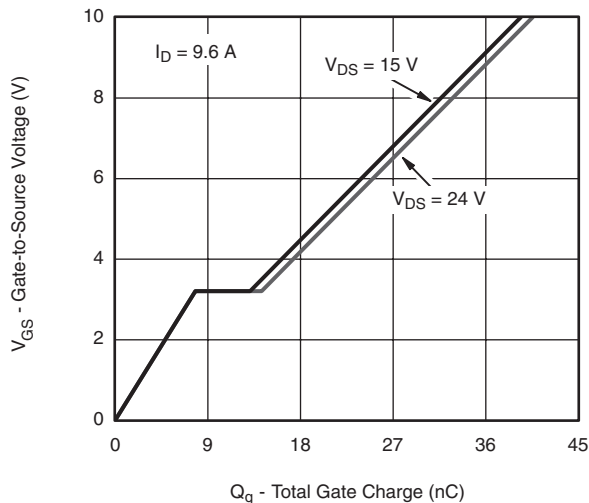
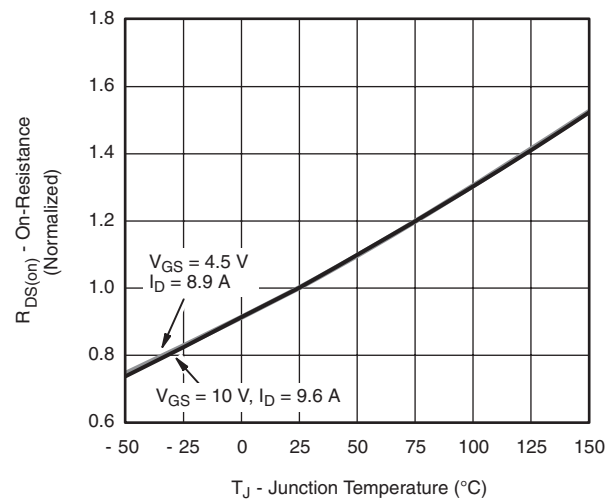
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Dynamic ^a							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 2\text{ }\Omega$ $I_D \cong 7.7\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	Ch-1		14	21	ns
			Ch-2		8	16	
Rise Time	t_r		Ch-1		8	16	
			Ch-2		10	20	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 2.8\text{ }\Omega$ $I_D \cong 5.3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	Ch-1		25	38	
			Ch-2		17	26	
Fall Time	t_f		Ch-1		9	18	
			Ch-2		8	15	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 2\text{ }\Omega$ $I_D \cong 7.7\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$	Ch-1		27	35	
			Ch-2		14	21	
Rise Time	t_r		Ch-1		15	23	
			Ch-2		12	18	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 2.8\text{ }\Omega$ $I_D \cong 5.3\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$	Ch-1		29	44	
			Ch-2		21	32	
Fall Time	t_f		Ch-1		11	17	
			Ch-2		11	17	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$	Ch-1			2.8	A
			Ch-2			2.6	
Pulse Diode Forward Current ^a	I_{SM}		Ch-1			60	
			Ch-2			30	
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$	Ch-1		0.57	0.68	V
		$I_S = 5.3\text{ A}$	Ch-2		0.8	1.2	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 $I_F = 7.7\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	Ch-1		26	39	ns
			Ch-2		17	26	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		15	23	nC
			Ch-2		8	16	
Reverse Recovery Fall Time	t_a	Channel-2 $I_F = 5.3\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	Ch-1		13		ns
			Ch-2		10		
Reverse Recovery Rise Time	t_b		Ch-1		13		
			Ch-2		7		

Notes:

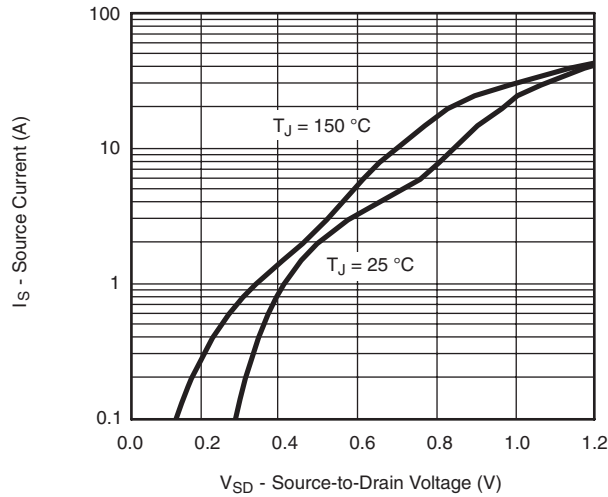
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

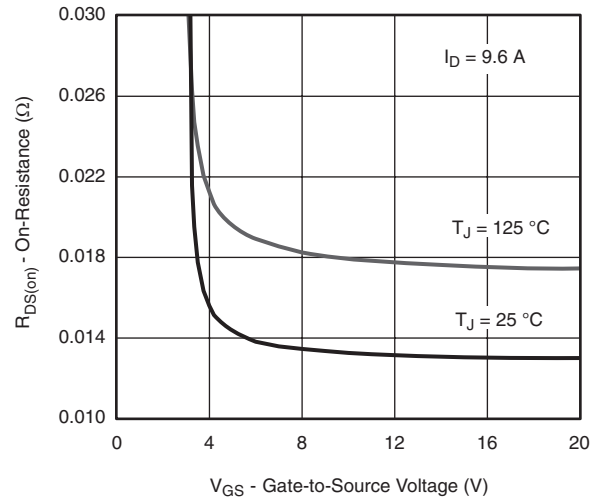
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

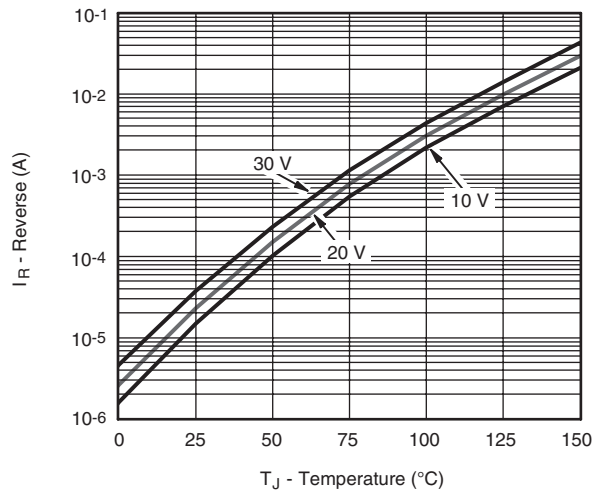
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



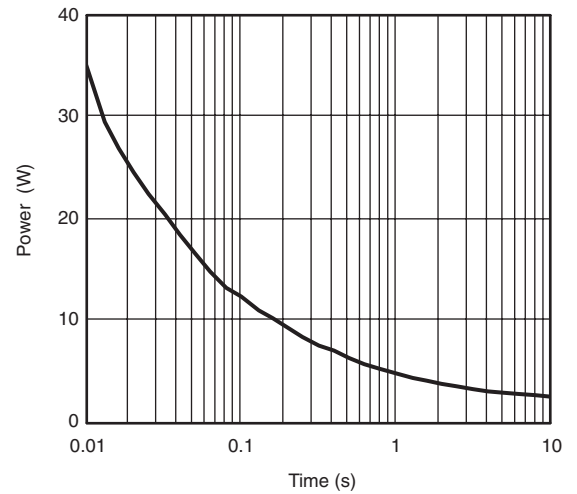
Source-Drain Diode Forward Voltage



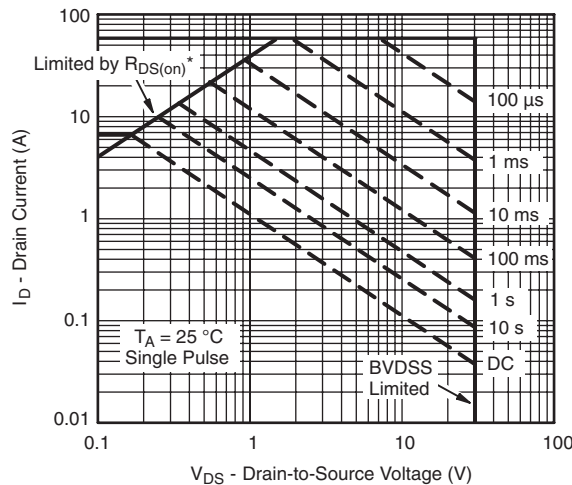
On-Resistance vs. Gate-to-Source Voltage



Reverse Current (Schottky)

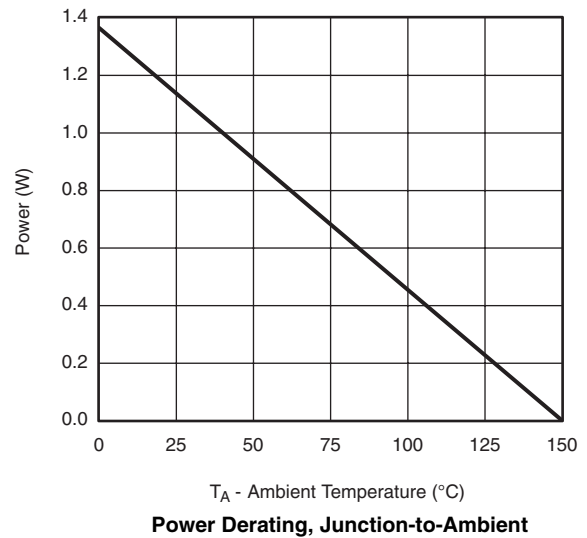
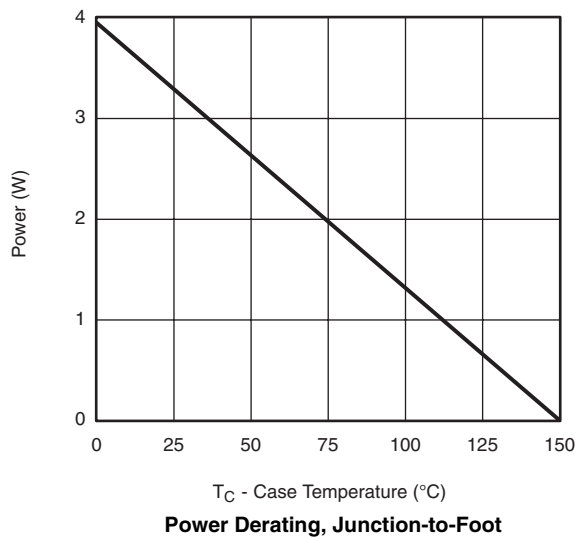
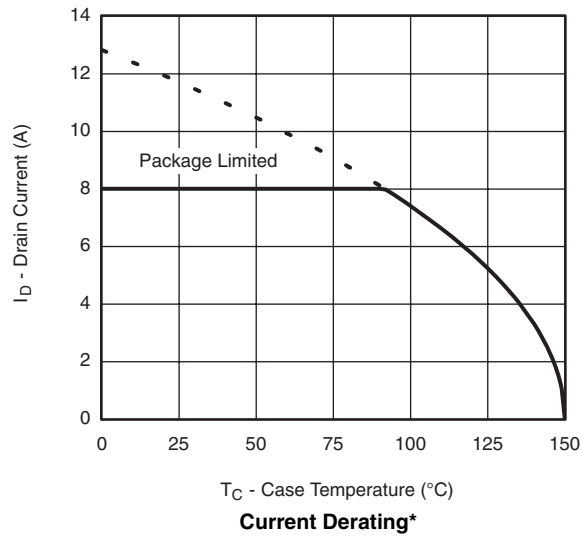


Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

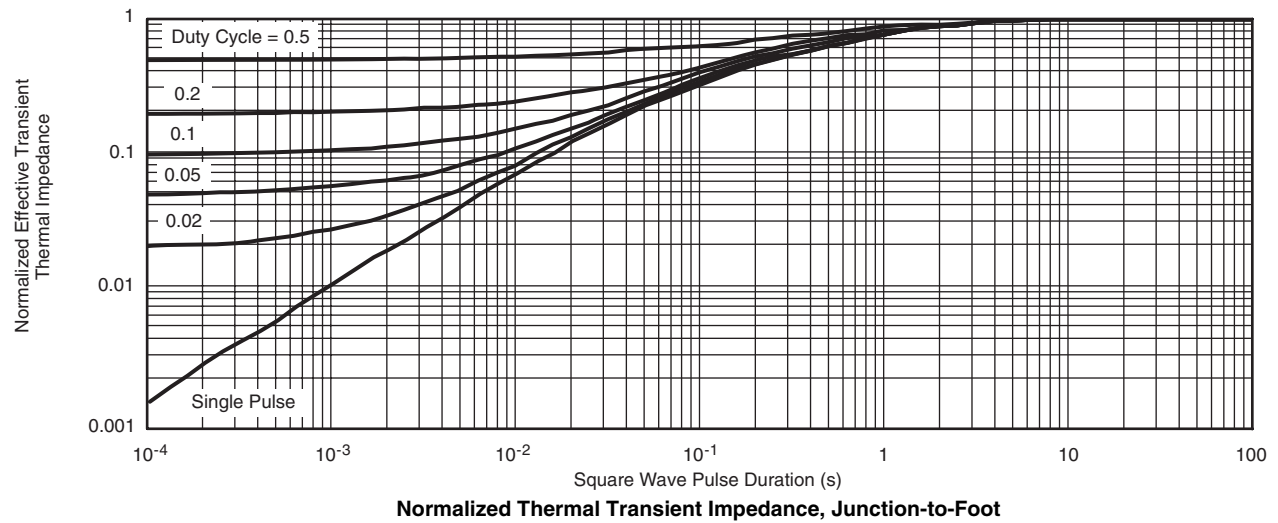
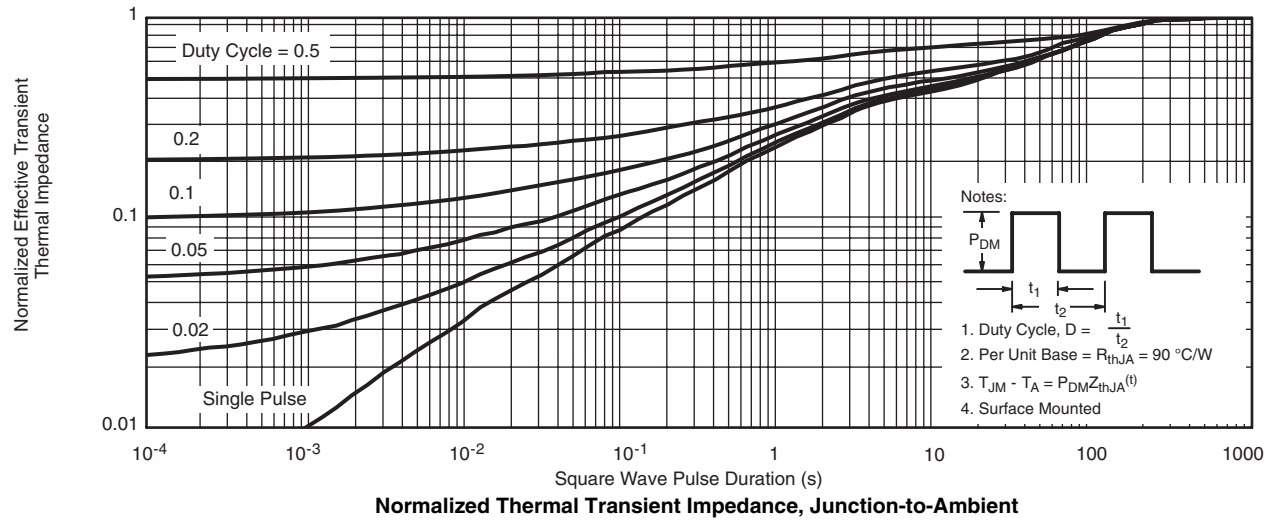
Safe Operating Area, Junction-to-Ambient

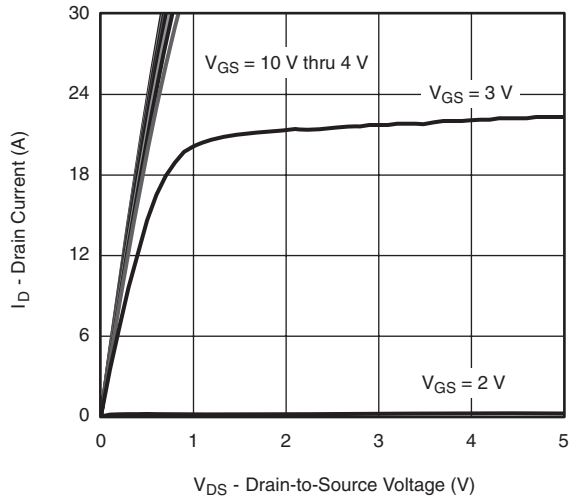
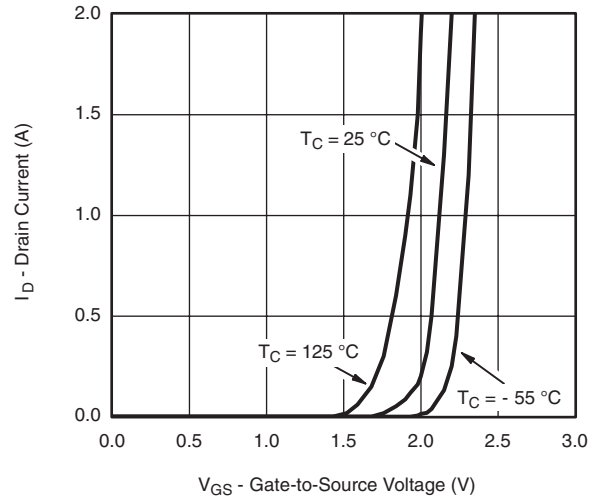
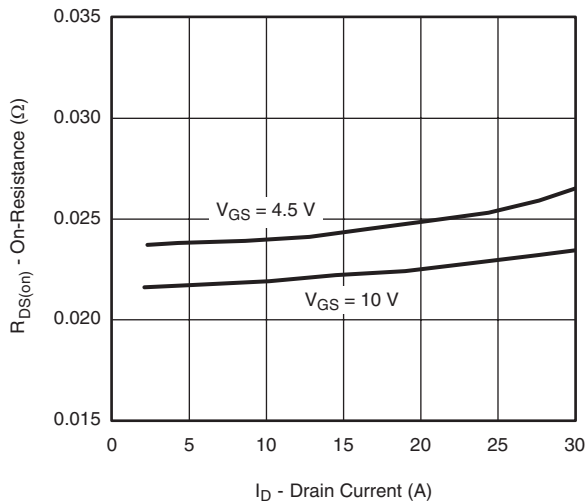
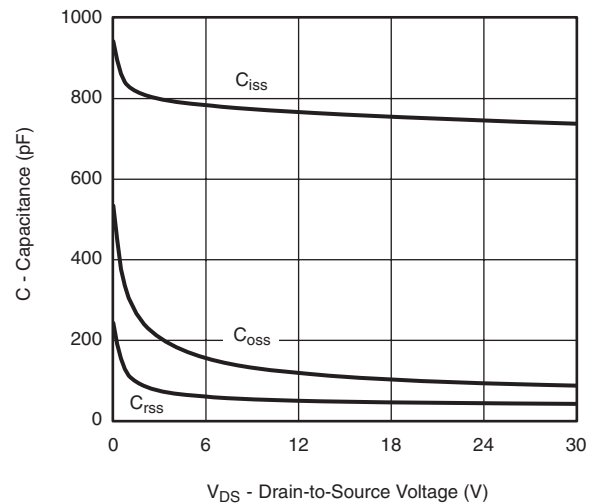
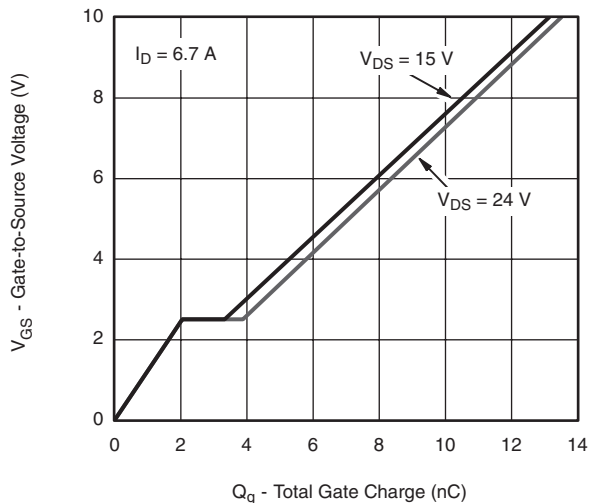
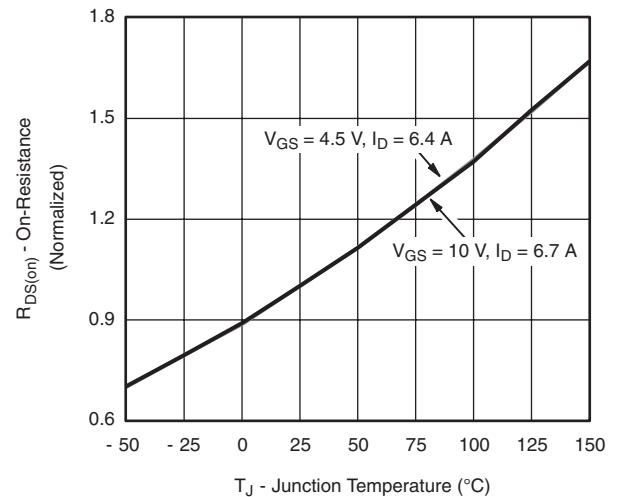
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



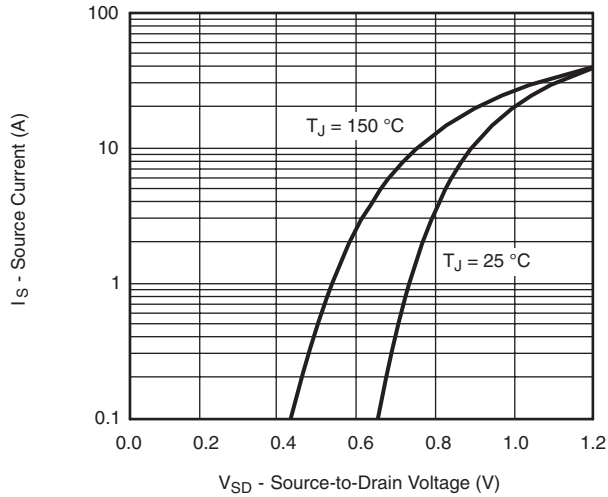
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



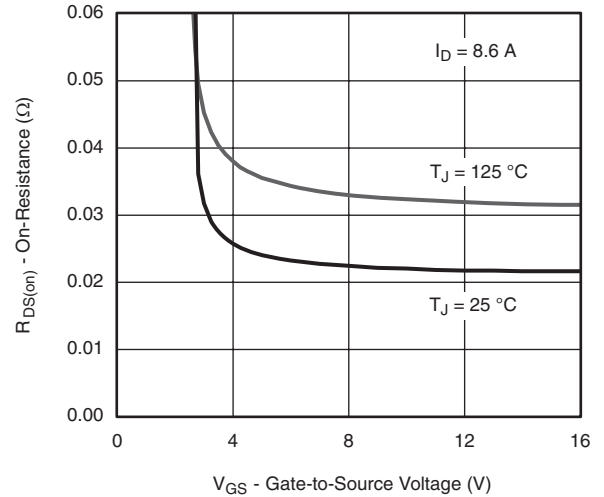
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**



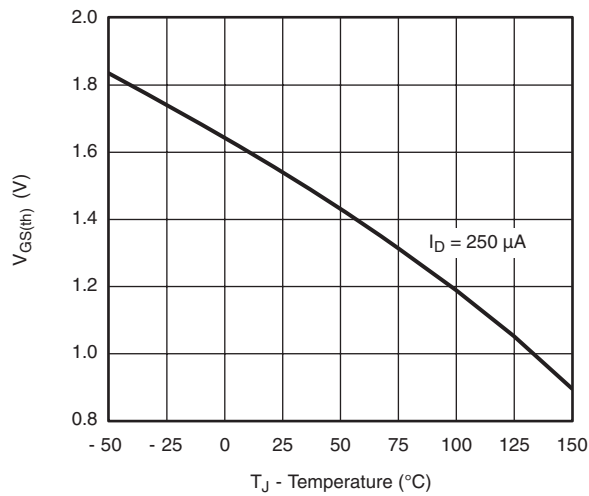
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



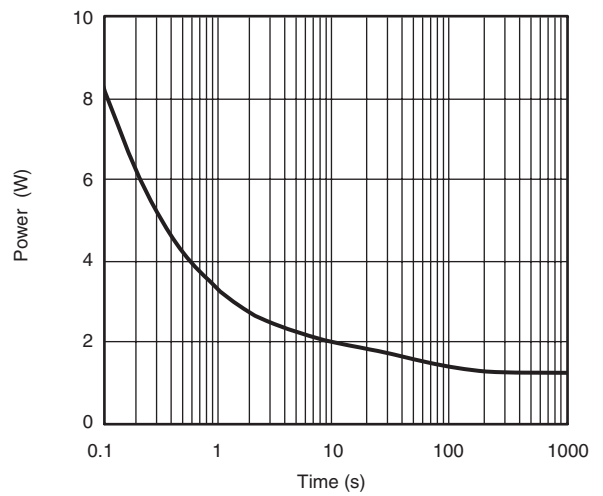
Source-Drain Diode Forward Voltage



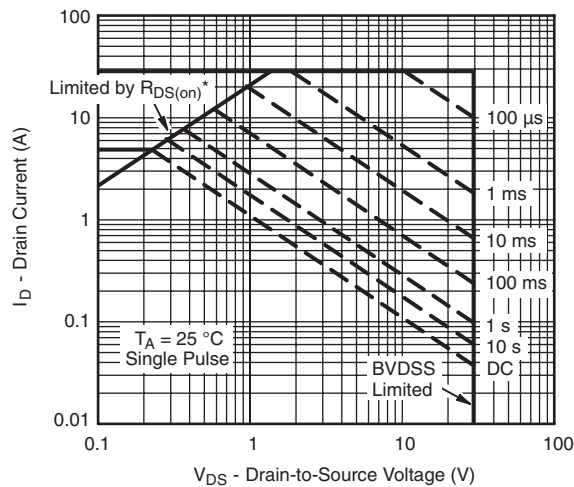
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

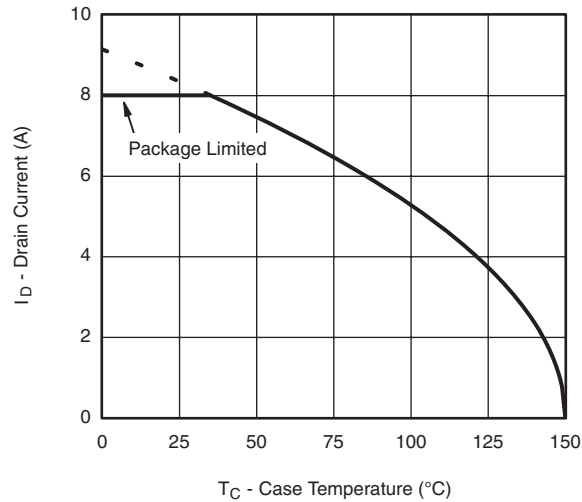
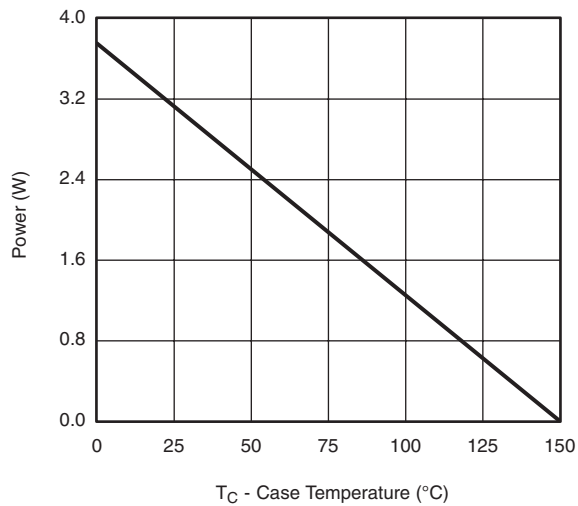
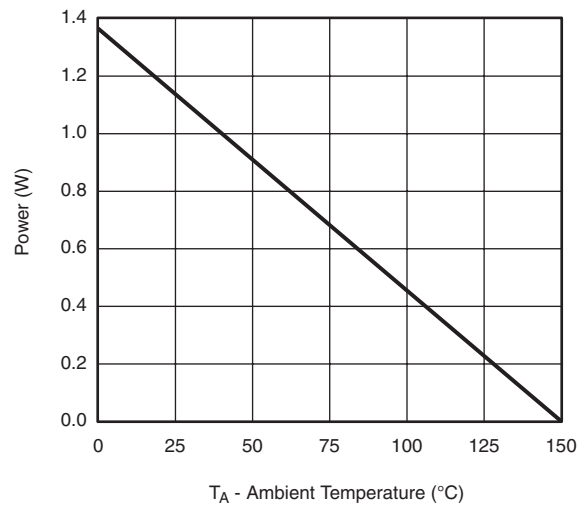


Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

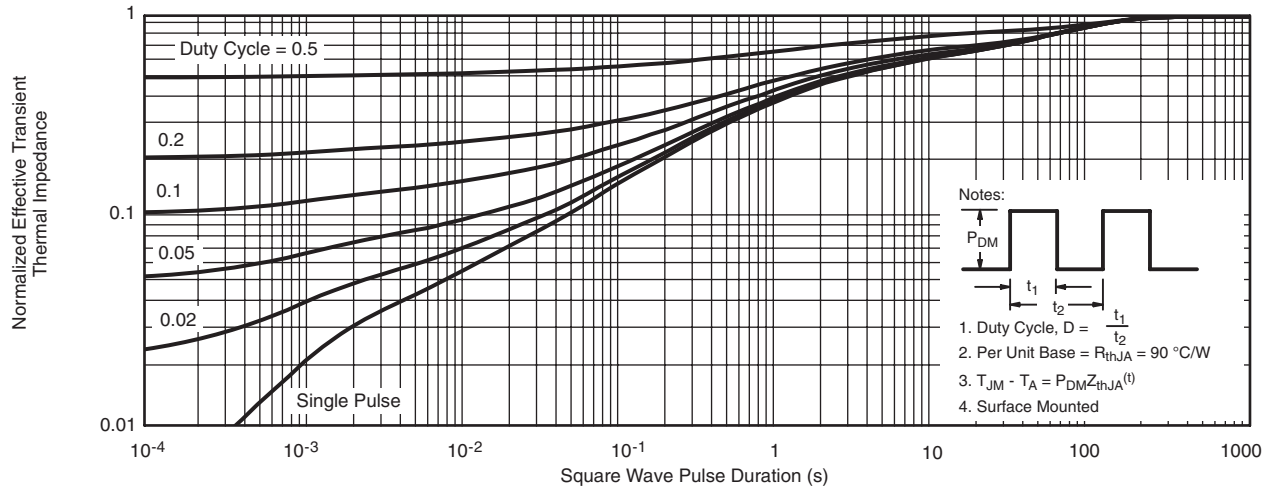
Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Current Derating*****Power Derating, Junction-to-Foot****Power Derating, Junction-to-Ambient**

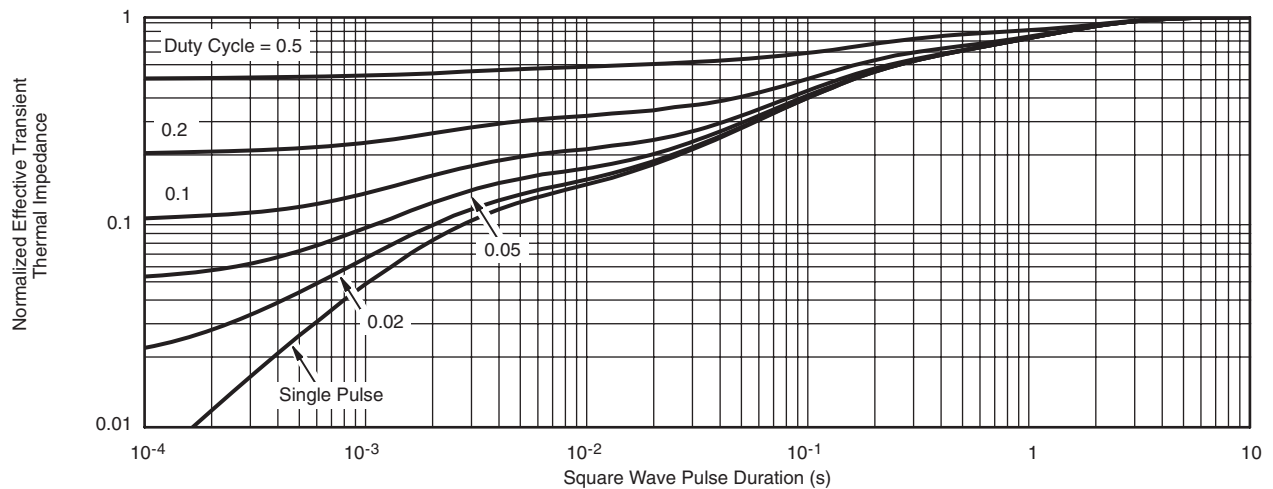
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

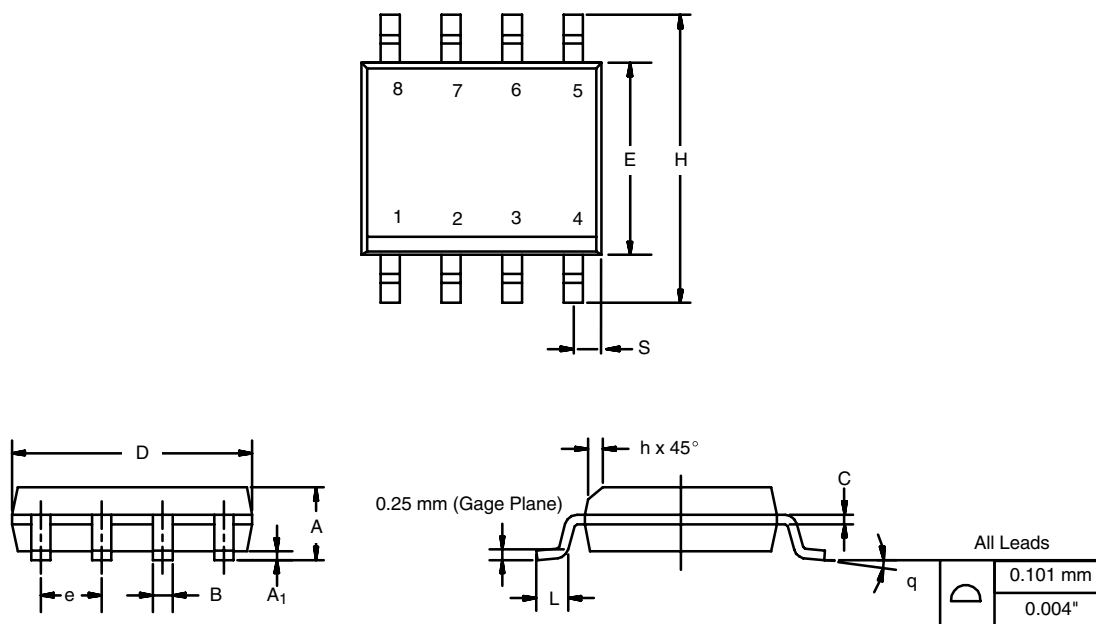


Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg268695.

SOIC (NARROW): 8-LEAD

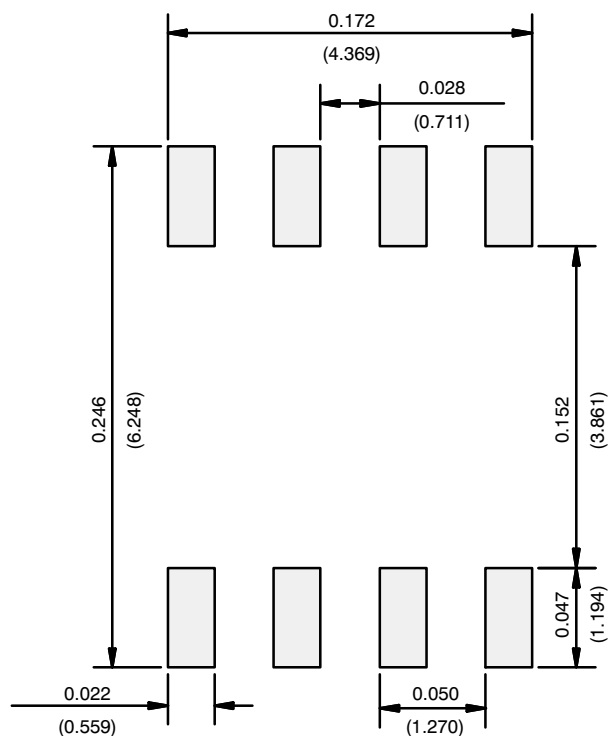
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

ECN: C-06527-Rev. I, 11-Sep-06
DWG: 5498

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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